PATENT COOPERATION TREATY

From the INTERNATIONAL SEARCHING AUTHORITY

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PCT



WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY (PCT Rule 43bis.1)

See paragraph 2 below

Date of mailing (day/month/year)

FOR FURTHER ACTION

12. 7. 2005

Applicant's or agent's file reference 10009228WO01

International filing date (day/month/year)

Priority date (day/month/year)

International application No. PCT/JP2005/006226

24.03.2005

30.03.2004

International Patent Classification (IPC) or both national classification and IPC Int.Cl.⁷ H01L27/146, 21/339, 21/8234, 27/088, 29/762

Applicant

CANON KABUSHIKI KAISHA

١.	This opini	on c	ontain	s inc	lica	uons	relating to	o me ioi	iowing	tems:

Box No. I Basis of the opinion

Box No. II Priority

Box No. III Non-establishment of opinion with regard to novelty, inventive step and industrial applicability

Box No. IV Lack of unity of invention

Box No. V Reasoned statement under Rule 43bis.1(a)(i) with regard to novelty, inventive step or industrial applicability;

citations and explanations supporting such statement

Box No. VI Certain documents cited

Box No. VII Certain defects in the international application

Box No. VIII Certain observations on the international application

2. FURTHER ACTION

If a demand for international preliminary examination is made, this opinion will be considered to be a written opinion of the International Preliminary Examining Authority ("IPEA") except that this does not apply where the applicant chooses an Authority other than this one to be the IPEA and the chosen IPEA has notified the International Bureau under Rule 66.1 bis(b) that written opinions of this International Searching Authority will not be so considered.

If this opinion is, as provided above, considered to be a written opinion of the IPEA, the applicant is invited to submit to the IPEA a written reply together, where appropriate, with amendments, before the expiration of 3 months from the date of mailing of Form PCT/ISA/220 or before the expiration of 22 months from the priority date, whichever expires later.

For further options, see Form PCT/ISA/220.

For further details, see notes to Form PCT/ISA/220.

Date of completion of this opinion 23.06.2005

Name and mailing address of the ISA/JP

Authorized officer

4L 8934

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Form PCT/ISA/237 (cover sheet) (January 2004)

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WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No. PCT/JP2005/006226

Box	No. 1	Basis of the opinion
1.		regard to the language, this opinion has been established on the basis of the international application in the language in it was filed, unless otherwise indicated under this item.
	Γ	This opinion has been established on the basis of a translation from the original language into the following language, which is the language of a translation furnished for the purposes of international search (under
	•	Rules 12.3 and 23.1(b)).
2.	With the	regard to any nucleotide and/or amino acid sequence disclosed in the international application and necessary to the ed invention, this opinion has been established on the basis of:
	a. typ	c of material
	Г	a sequence listing
•	Γ	table(s) related to the sequence listing
	b. for	mat of material
	Γ	in written format
		in computer readable form
	c. tim	e of filing/furnishing
	Γ	••
	Γ	•
	Γ	furnished subsequently to this Authority for the purposes of search.
3.	Γ	In addition, in the case that more than one version or copy of a sequence listing and/or table relating thereto has been filed or furnished, the required statements that the information in the subsequent or additional copies is identical to that in the application as filed or does not go beyond the application as filed, as appropriate, were furnished.
4.	Addit	tional comments:
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WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No.

PCT/JP2005/006226

Reasoned statement under Rule 43bis.1(a)(i) with regard to novelty, inventive step or industrial applicability; Box No. V citations and explanations supporting such statement Statement YES 2-10 Novclty (N) Claims Claims YES 2-10 Claims Inventive step (IS) Claims YES 1-10 Industrial applicability (IA) Claims NO Claims

2. Citations and explanations

D1: JP 2000-353756 A (TOSHIBA CORPORATION) 2000.12.19, The whole document (Family: none)

D2: JP 2002-329793 A (MITSUBISHI ELECTRIC CORPORATION) 2002.11.15, The whole document (Family: none)

D3: JP 2000-077613 A (NEC CORPORAION) 2000.03.14, The whole document

D4: JP 7-321220 A (NIPPON DENSO CO., Ltd.) 1995.12.08, The whole document ,Fig.5 (Family: none)

D5: JP 2004-158508 A (NIPPON TEXAS INSTRUMENTS INCORPORATED) 2004.06.03, The whole document (Family: none)

D6: JP 2003-333431 A (VICTOR COMPANY OF JAPAN, LTD.) 2003.11.21, The whole document (Family: none)

The subject matter of claim 1 is disclosed in the document D1 cited in the ISR. As shown in Fig.9 (a) and (b), both the surface channel type n type MOS transistor and the buried channel n type transistor have n type impurity region below its gate electrode of said surface channel type and buried channel type MOS transistors.

The subject matter of claims 2 to 10 meets the requirements of novelty and an inventive step.

The closest prior art document D1 discloses a semiconductor apparatus but doesn't disclose a solid state image pickup device.

The prior art documents D5 and D6 disclose a solid state image pickup device but don't disclose the device comprising a pixel having a plurality of MOS transistors, and an impurity region which conductive type is the same as said MOS transistors is provided below a gate electrode and between source and drain region of said MOS transistors

WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No.

PCT/JP2005/006226

Box No. VIII Certain observations on the international application

The following observations on the clarity of the claims, description, and drawings or on the question whether the claims are fully supported by the description, are made:

The term ["between source and drain regions ...] used in Claim 1 and ["below a gate and between source and drain regions of said buried channel type and surface channel type MOS transistors ...] used in Claim 2 render the definition of the subject matter of said claim unclear for the following reason:

Consequently they render the position of a first conductive type impurity region unclear.